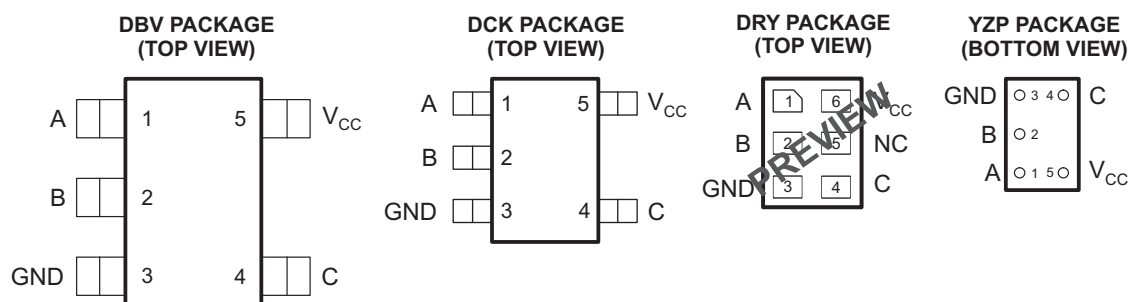


SINGLE BILATERAL ANALOG SWITCH

FEATURES

- Available in the Texas Instruments NanoFree™ Package
- Wide V_{CC} Range of 0.8 V to 2.7 V
- Sub-1-V Operable
- Low Power Consumption, 10- μ A Max I_{CC}
- High On-Off Output Voltage Ratio
- High Degree of Linearity
- High Speed – Max 0.2 ns ($V_{CC} = 1.8$ V, $C_L = 15$ pF)
- Low On-State Impedance – Typically 9 Ω ($V_{CC} = 2.3$ V)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)



See mechanical drawings for dimensions.
NC– No internal connection

DESCRIPTION/ORDERING INFORMATION

This single analog switch is operational at 0.8-V to 2.7-V V_{CC} , but is designed specifically for 1.65-V to 1.95-V V_{CC} operation.

The SN74AUC1G66 can handle both analog and digital signals. The combined AC and DC signal has to be between V_{CC} and GND for it to be transmitted in either direction.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoFree is a trademark of Texas Instruments.

UNLESS OTHERWISE NOTED this document contains PRODUCTION DATA information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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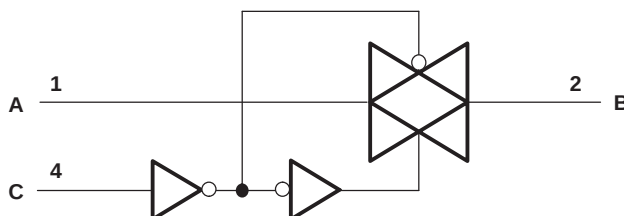
ORDERING INFORMATION

T_A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
–40°C to 85°C	NanoFree™ WCSP (DSBGA) – YZP (Pb-free)	Reel of 3000	SN74AUC1G66YZPR	– – _U6_
	SON – DRY	Reel of 5000	SN74AUC1G66DRYR	PREVIEW
	SOT (SOT-23) – DBV	Reel of 3000	SN74AUC1G66DBVR	U66_
	SOT (SC-70) – DCK	Reel of 3000	SN74AUC1G66DCKR	U6_

- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) DBV/DCK/DRY: The actual top-side marking has one additional character that designates the assembly/test site.
YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.

FUNCTION TABLE

CONTROL INPUT (C)	SWITCH
L	OFF
H	ON

LOGIC DIAGRAM (POSITIVE LOGIC)**Absolute Maximum Ratings⁽¹⁾**

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		−0.5	3.6	V
V _I	Input voltage range ⁽²⁾		−0.5	3.6	V
V _{I/O}	Switch I/O voltage range ⁽²⁾⁽³⁾		−0.5	V _{CC} + 0.5	V
I _{IK}	Control input clamp current	V _I < 0		−50	mA
I _{IOK}	I/O port diode current	V _{I/O} < 0 or V _{I/O} > V _{CC}		±50	mA
I _T	On-state switch current	V _{I/O} = 0 to V _{CC}		±50	mA
Continuous current through V _{CC} or GND				±100	mA
θ _{JA}	Package thermal impedance ⁽⁴⁾	DBV package		206	°C/W
		DCK package		252	
		DRY package		234	
		YZP package		123	
T _{stg}	Storage temperature range		−65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		0.8	2.7	V
V _{IH}	High-level input voltage	V _{CC} = 0.8 V	V _{CC}		V
		V _{CC} = 1.1 V to 1.95 V	0.65 × V _{CC}		
		V _{CC} = 2.3 V to 2.7 V	1.7		
V _{IL}	Low-level input voltage	V _{CC} = 0.8 V	0		V
		V _{CC} = 1.1 V to 1.95 V	0.35 × V _{CC}		
		V _{CC} = 2.3 V to 2.7 V	0.7		
V _{I/O}	I/O port voltage		0	V _{CC}	V
V _I	Control input voltage		0	3.6	V
Δt/Δv	Input transition rise or fall rate			20	ns/V
T _A	Operating free-air temperature		−40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
r _{on}	On-state switch resistance V _I = V _{CC} or GND, V _C = V _{IH} (see Figure 1)	I _S = 4 mA I _S = 8 mA	1.65 V 2.3 V	10 9	20 15	Ω
r _{on(p)}	Peak on resistance V _I = V _{CC} to GND, V _C = V _{IH} (see Figure 1)	I _S = 4 mA I _S = 8 mA	1.65 V 2.3 V	32 15	80 20	Ω
I _{S(off)}	Off-state switch leakage current V _I = V _{CC} and V _O = GND, or V _I = GND and V _O = V _{CC} , V _C = V _{IL} (see Figure 2)	2.7 V		±1 ±0.1 ⁽¹⁾		μA
I _{S(on)}	On-state switch leakage current V _I = V _{CC} or GND, V _C = V _{IH} , V _O = Open (see Figure 3)	2.7 V		±1 ±0.1 ⁽¹⁾		μA
I _I	Control input current V _I = V _{CC} or GND	0 to 2.7 V			±5	μA
I _{CC}	Supply current V _I = V _{CC} or GND, I _O = 0	0.8 V to 2.7 V			10	μA
C _{ic}	Control input capacitance	2.5 V		2		pF
C _{io(off)}	Switch input/output capacitance	2.5 V		3.5		pF
C _{io(on)}	Switch input/output capacitance	2.5 V		7		pF

(1) All typical values are at T_A = 25°C.

Switching Characteristics

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	UNIT
			TYP	MIN MAX	MIN MAX	MIN TYP MAX	MIN MAX	
t _{pd} ⁽¹⁾	A or B	B or A	0.9	0.3	0.2	0.2	0.1	ns
t _{en}	C	A or B	4.1	0.5 2.6	0.5 1.7	0.5 0.8 1.1	0.5 1	ns
t _{dis}	C	A or B	5	0.7 3.6	0.5 2.6	0.5 1.7 2.9	0.5 2.2	ns

(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 30$ pF (unless otherwise noted) (see [Figure 4](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$			$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$		UNIT
			MIN	TYP	MAX	MIN	MAX	
$t_{pd}^{(1)}$	A or B	B or A			0.3		0.3	ns
t_{en}	C	A or B	0.5	1.4	2.3	0.8	1.4	ns
t_{dis}	C	A or B	0.5	1.7	2.9	0.5	1.5	ns

- (1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

Analog Switch Characteristics

 $T_A = 25^{\circ}\text{C}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V_{CC}	TYP	UNIT
Frequency response ⁽¹⁾ (switch ON)	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = \text{sine wave}$ (see Figure 5)	0.8 V	60	MHz
				1.1 V	60	
				1.4 V	80	
				1.65 V	120	
				2.3 V	170	
			$C_L = 5\text{ pF}$, $R_L = 50\ \Omega$, $f_{in} = \text{sine wave}$ (see Figure 5)	0.8 V	>500	
				1.1 V	>500	
				1.4 V	>500	
				1.65 V	>500	
				2.3 V	>500	
Crosstalk (control input to signal output)	C	A or B	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = 1\text{ MHz}$ (square wave) (see Figure 6)	0.8 V	9	mV
				1.1 V	14	
				1.4 V	15	
				1.65 V	16	
				2.3 V	20	
Feedthrough attenuation ⁽²⁾ (switch OFF)	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 600\ \Omega$, $f_{in} = 1\text{ MHz}$ (sine wave) (see Figure 7)	0.8 V	–60	dB
				1.1 V	–60	
				1.4 V	–60	
				1.65 V	–60	
				2.3 V	–60	
			$C_L = 5\text{ pF}$, $R_L = 50\ \Omega$, $f_{in} = 1\text{ MHz}$ (sine wave) (see Figure 7)	0.8 V	–55	
				1.1 V	–55	
				1.4 V	–55	
				1.65 V	–55	
				2.3 V	–55	
Sine-wave distortion	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 10\text{ k}\Omega$, $f_{in} = 1\text{ kHz}$ (sine wave) (see Figure 8)	0.8 V	7.5	%
				1.1 V	0.16	
				1.4 V	0.04	
				1.65 V	0.03	
				2.3 V	0.02	
	A or B	B or A	$C_L = 50\text{ pF}$, $R_L = 10\text{ k}\Omega$, $f_{in} = 10\text{ kHz}$ (sine wave) (see Figure 8)	0.8 V	4.2	
				1.1 V	0.2	
				1.4 V	0.03	
				1.65 V	0.02	
				2.3 V	0.02	

(1) Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads –3 dB.

(2) Adjust f_{in} voltage to obtain 0 dBm at input.

Operating Characteristics

 $T_A = 25^{\circ}\text{C}$

PARAMETER	TEST CONDITIONS	$V_{CC} = 0.8\text{ V}$	$V_{CC} = 1.2\text{ V}$	$V_{CC} = 1.5\text{ V}$	$V_{CC} = 1.8\text{ V}$	$V_{CC} = 2.5\text{ V}$	UNIT
		TYP	TYP	TYP	TYP	TYP	
C_{pd} Power dissipation capacitance	$f = 10\text{ MHz}$	3	3	3	3	3	pF

PARAMETER MEASUREMENT INFORMATION

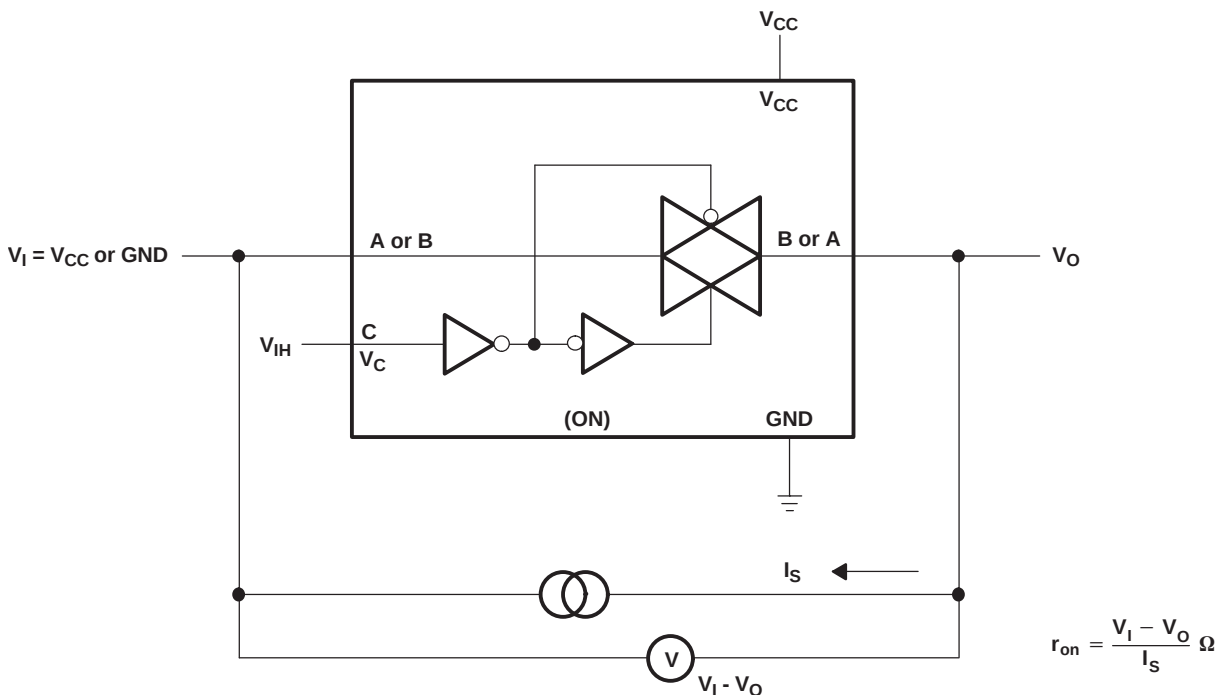


Figure 1. On-State Resistance Test Circuit

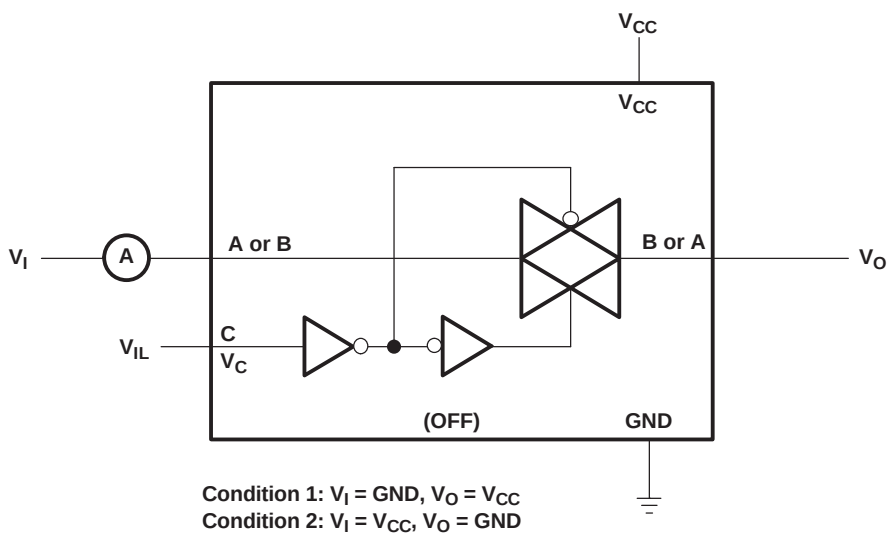


Figure 2. Off-State Switch Leakage-Current Test Circuit

PARAMETER MEASUREMENT INFORMATION (Continued)

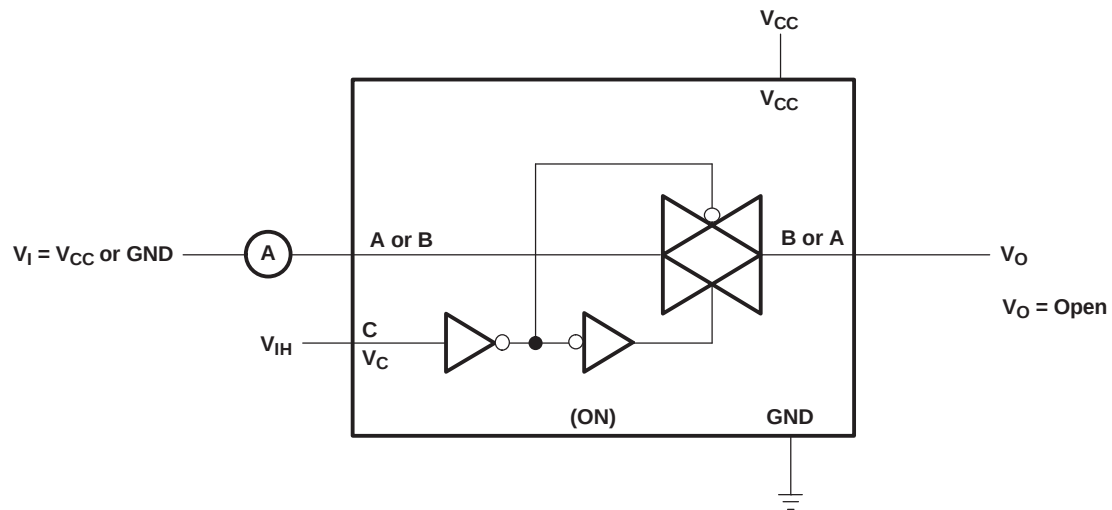
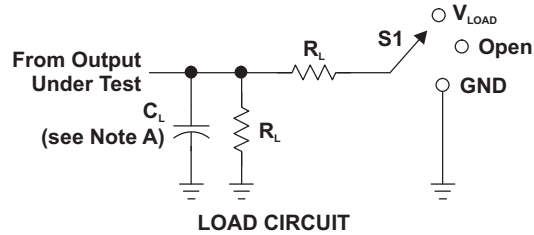


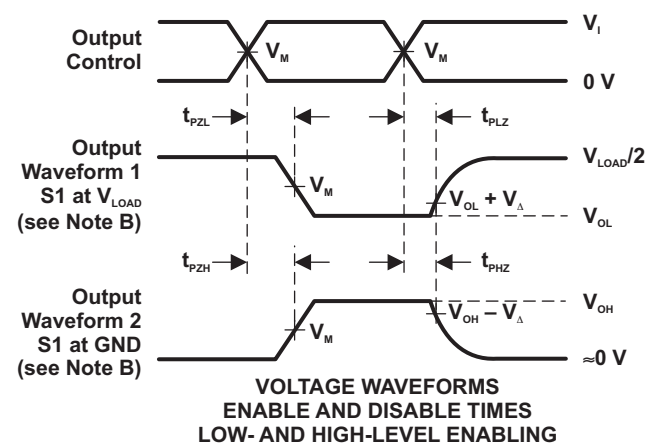
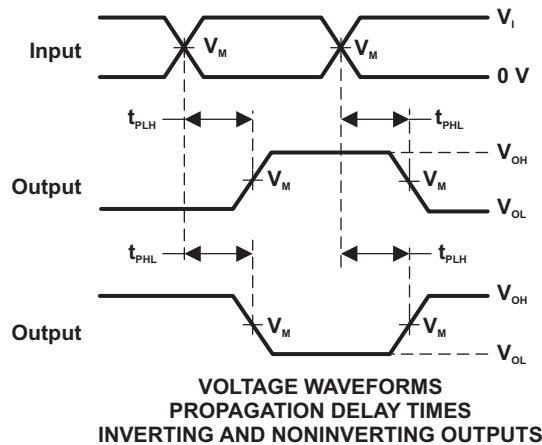
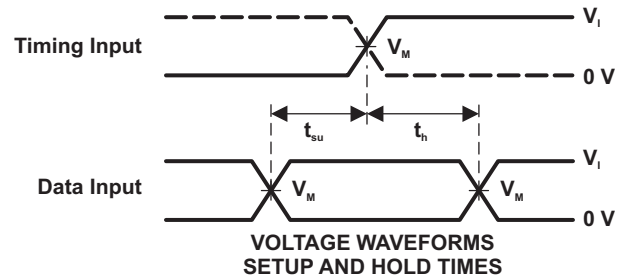
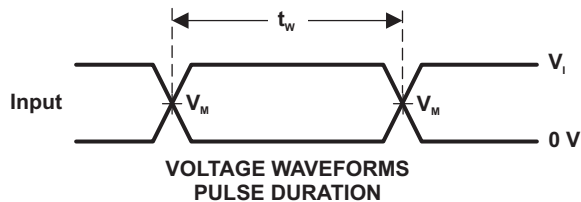
Figure 3. On-State Leakage-Current Test Circuit

PARAMETER MEASUREMENT INFORMATION (Continued)



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_i	t_i/t_f					
0.8 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k Ω	0.1 V
1.2 V $\pm$ 0.1 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k Ω	0.1 V
1.5 V $\pm$ 0.1 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k Ω	0.1 V
1.8 V $\pm$ 0.15 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k Ω	0.15 V
2.5 V $\pm$ 0.2 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k Ω	0.15 V
1.8 V $\pm$ 0.15 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
2.5 V $\pm$ 0.2 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR $\leq$ 10 MHz, $Z_o = 50 \Omega$, Slew rate $\geq$ 1 V/ns.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 4. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION (Continued)

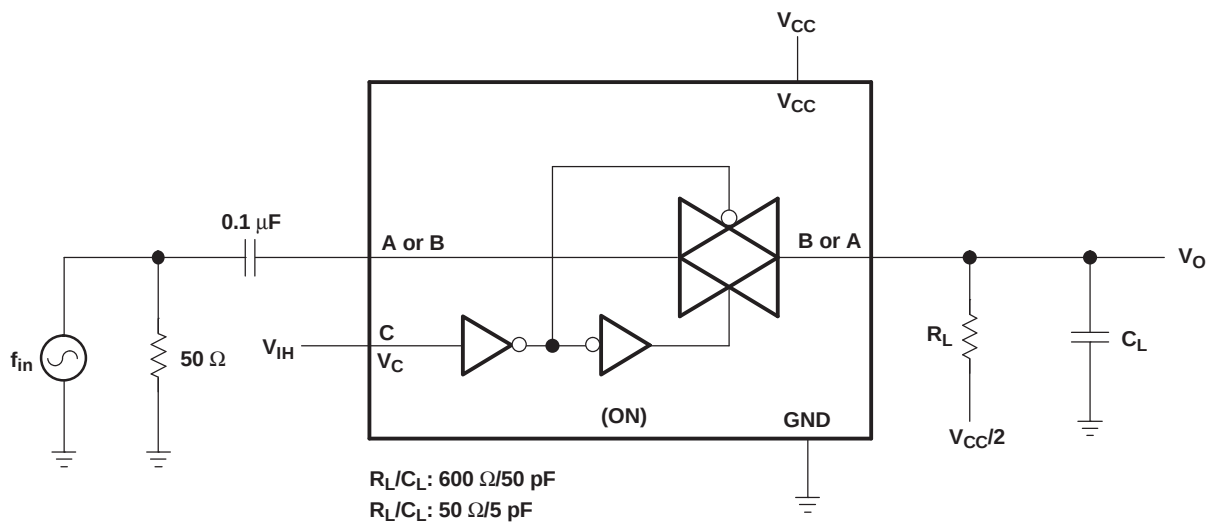


Figure 5. Frequency Response (Switch ON)

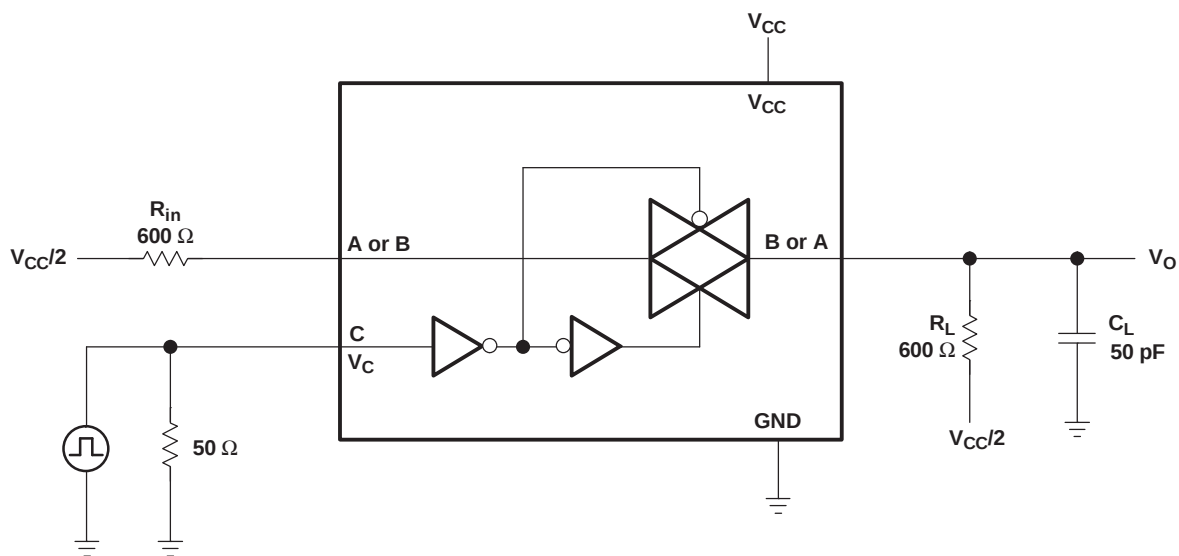


Figure 6. Crosstalk (Control Input – Switch Output)

PARAMETER MEASUREMENT INFORMATION (Continued)

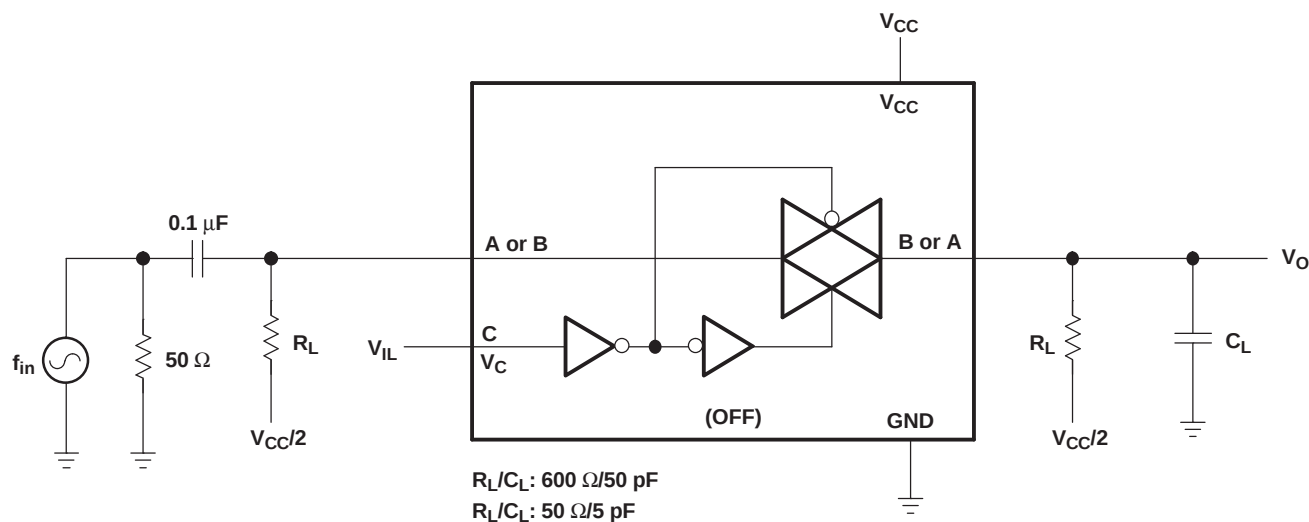


Figure 7. Feedthrough (Switch OFF)

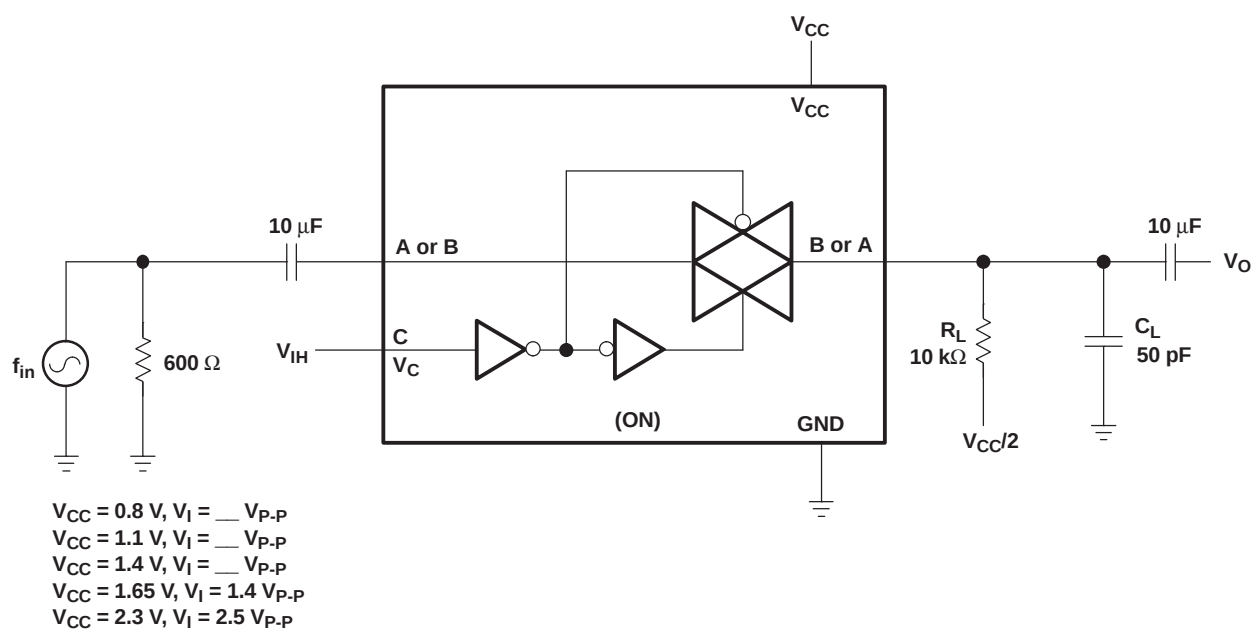


Figure 8. Sine-Wave Distortion

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AUC1G66DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 85	(U66F ~ U66R)	Samples
SN74AUC1G66DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	U66F	Samples
SN74AUC1G66DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(U65 ~ U6F ~ U6R)	Samples
SN74AUC1G66DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(U65 ~ U6F ~ U6R)	Samples
SN74AUC1G66YZPR	ACTIVE	DSBGA	YZP	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(U67 ~ U6N)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUC1G66DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AUC1G66DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AUC1G66YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

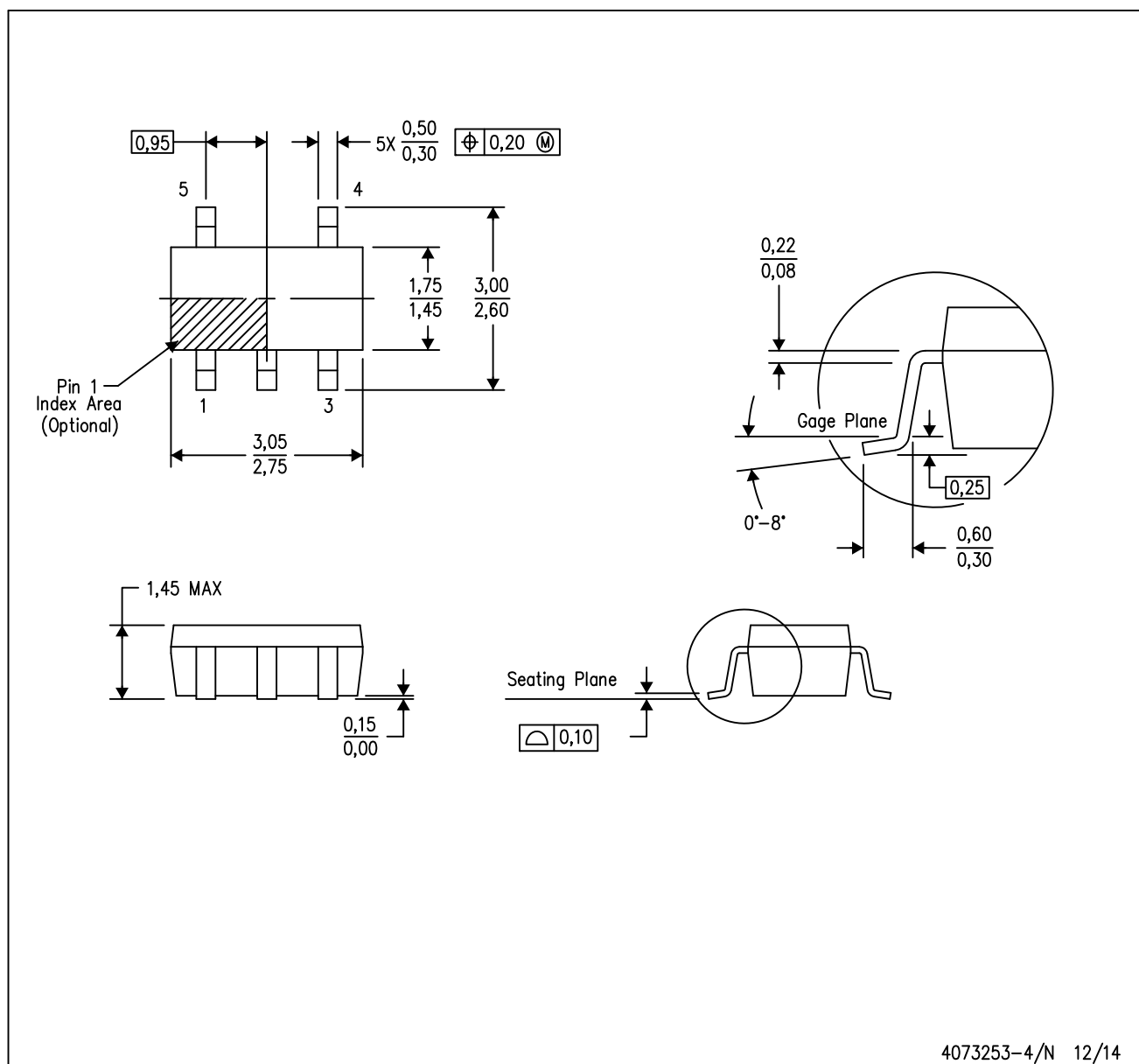


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AUC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUC1G66YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - Falls within JEDEC MO-178 Variation AA.

DBV (R-PDSO-G5)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
 - D. Publication IPC-7351 is recommended for alternate designs.
 - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



4093553-3/G 01/2007

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

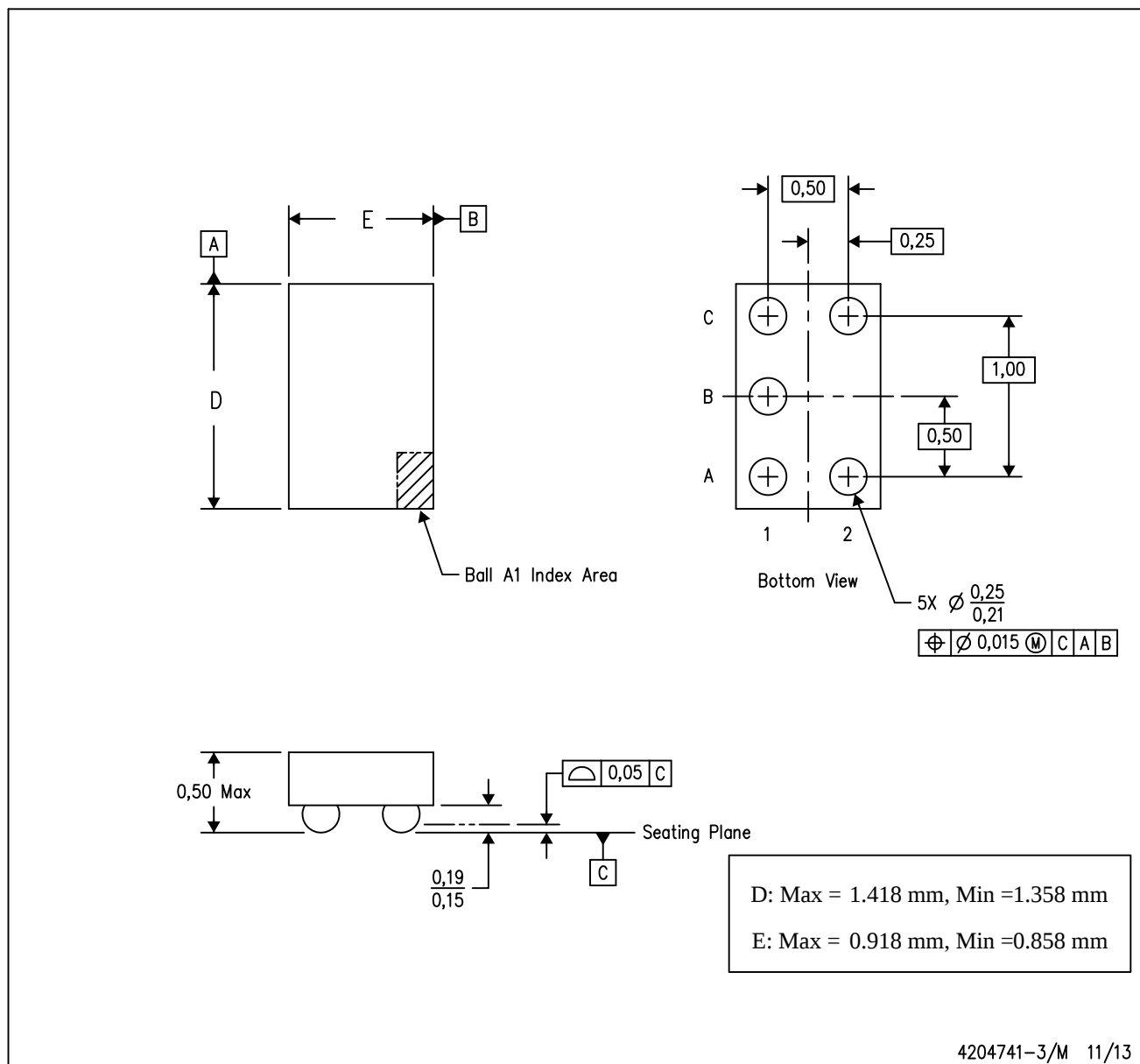
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
 - D. Publication IPC-7351 is recommended for alternate designs.
 - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

YZP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.

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